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Autore	Morkoc Hadis
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3.2.3.2 Surface Preparation of SiC for Epitaxy

Sommario/riassunto

The three volumes of this handbook treat the fundamentals, technology and nanotechnology of nitride semiconductors with an extraordinary clarity and depth. They present all the necessary basics of semiconductor and device physics and engineering together with an extensive reference section. Volume 1 deals with the properties and growth of GaN. The deposition methods considered are: hydride VPE, organometallic CVD, MBE, and liquid/high pressure growth. Additionally, extended defects and their electrical nature, point defects, and doping are reviewed.